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## PEMB11; PUMB11

# PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$

Rev. 3 — 30 November 2011

**Product data sheet** 

## 1. Product profile

#### 1.1 General description

PNP/PNP Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

7,000			NPN/NPN	Package	
	NXP	JEITA	complement	complement	configuration
PEMB11	SOT666	-	PEMD3	PEMH11	ultra small and flat lead
PUMB11	SOT363	SC-88	PUMD3	PUMH11	very small

#### 1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

#### 1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

#### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transist	or					
$V_{CEO}$	collector-emitter voltage	open base	-	-	-50	V
I <sub>O</sub>	output current		-	-	-100	mA
R1	bias resistor 1 (input)		7	10	13	kΩ
R2/R1	bias resistor ratio		0.8	1.0	1.2	



## 2. Pinning information

Table 3. Pinning

Table 5.	ı ıııınıy		
Pin	Description	Simplified outline	Graphic symbol
1	GND (emitter) TR1		
2	input (base) TR1	6 5 4	6 5 4
3	output (collector) TR2		
4	GND (emitter) TR2		R1 R2
5	input (base) TR2		TR1
6	output (collector) TR1	001aab555	1 2 3
			006aaa212

## 3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
PEMB11	<b>'-</b>	plastic surface-mounted package; 6 leads	SOT666
PUMB11	SC-88	plastic surface-mounted package; 6 leads	SOT363

## 4. Marking

Table 5. Marking codes

Type number	Marking code <sup>[1]</sup>
PEMB11	B1
PUMB11	B*1

<sup>[1] \* =</sup> placeholder for manufacturing site code.

## 5. Limiting values

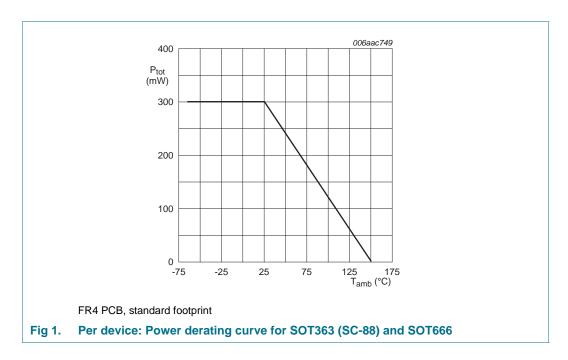
Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
$V_{CBO}$	collector-base voltage	open emitter	-	-50	V
$V_{CEO}$	collector-emitter voltage	open base	-	-50	V
$V_{EBO}$	emitter-base voltage	open collector	-	-10	V
VI	input voltage	input voltage			
	positive		-	+10	V
	negative		-	-40	V
I <sub>O</sub>	output current		-	-100	mA
I <sub>CM</sub>	peak collector current		-	-100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	<u>[1]</u>		
	PEMB11 (SOT666)		[2] _	200	mW
	PUMB11 (SOT363)		-	200	mW
Per device	)				
P <sub>tot</sub>	total power dissipation	$T_{amb} \leq 25 ^{\circ}C$	<u>[1]</u>		
	PEMB11 (SOT666)		[2] _	300	mW
	PUMB11 (SOT363)		-	300	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.



## 6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	sistor					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u>			
	PEMB11 (SOT666)		[2] _	-	625	K/W
	PUMB11 (SOT363)		-	-	625	K/W
Per devi	ce					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u>			
	PEMB11 (SOT666)		[2] _	-	417	K/W
	PUMB11 (SOT363)		-	-	417	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.

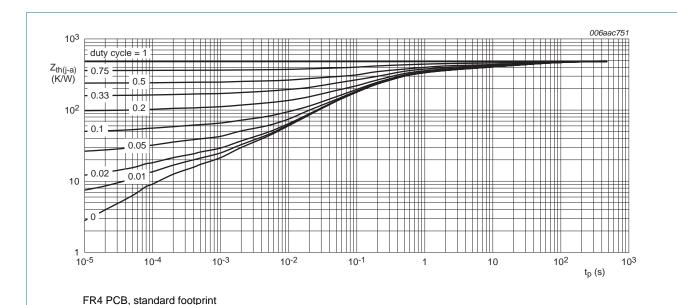


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for PEMB11 (SOT666); typical values

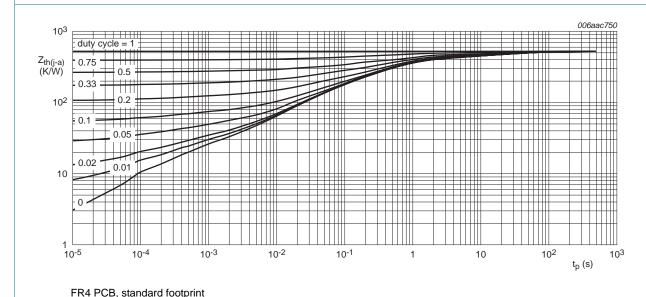


Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for PUMB11 (SOT363); typical values

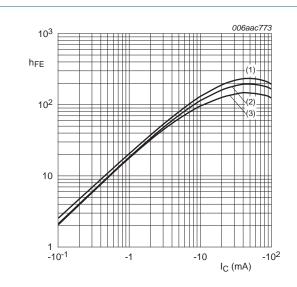
## 7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I <sub>CEO</sub>	collector-emitter	$V_{CE} = -30 \text{ V}; I_B = 0 \text{ A}$	-	-	-1	μΑ
	cut-off current	$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	<b>-</b> 5	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-400	μΑ
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -5 \text{ mA}$	-30	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	-	-	-150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = -5 \text{ V}; I_C = -100 \mu\text{A}$	-	-1.1	-0.8	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = -0.3 \text{ V}; I_{C} = -10 \text{ mA}$	-2.5	-1.8	-	V
R1	bias resistor 1 (input)		7	10	13	$k\Omega$
R2/R1	bias resistor ratio		8.0	1.0	1.2	
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = I_e = 0 \text{ A};$ f = 1 MHz	-	-	3	pF
f <sub>T</sub>	transition frequency	$V_{CB} = -5 \text{ V}; I_C = -10 \text{ mA};$ f = 100 MHz	<u>[1]</u> -	180	-	MHz

<sup>[1]</sup> Characteristics of built-in transistor.



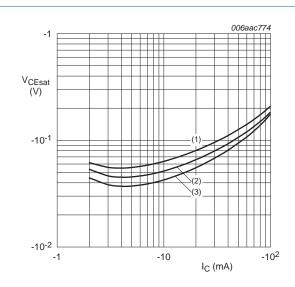
$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 4. DC current gain as a function of collector current; typical values



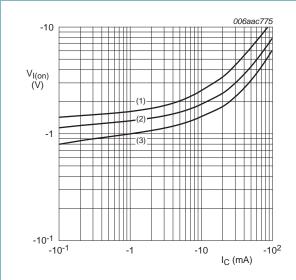
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values

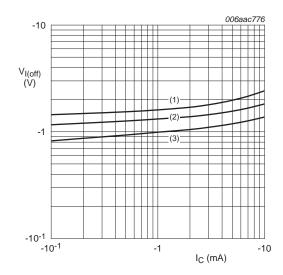


$$V_{CE} = -0.3 \text{ V}$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

Fig 6. On-state input voltage as a function of collector current; typical values



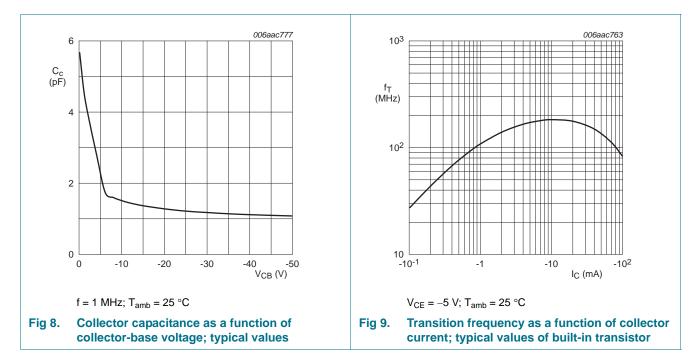
$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 7. Off-state input voltage as a function of collector current; typical values

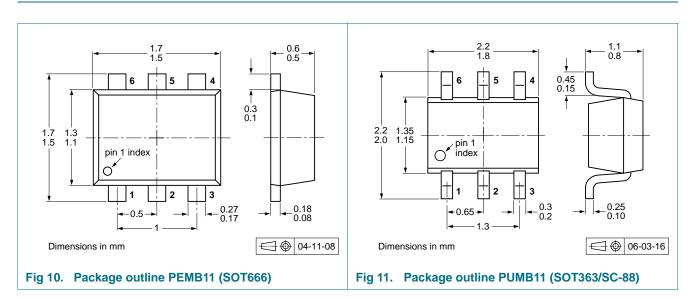


## 8. Test information

#### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 9. Package outline



PEMB11 PUMB11

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## 10. Packing information

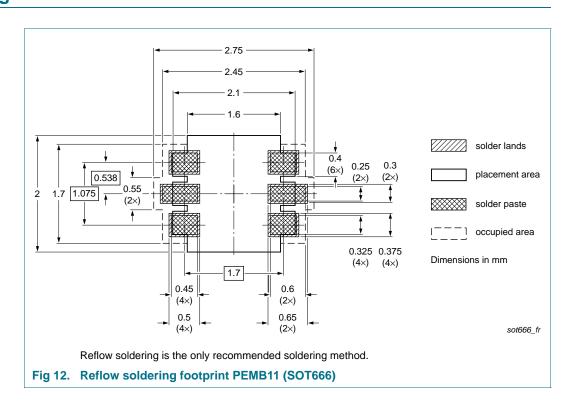
Table 9. Packing methods

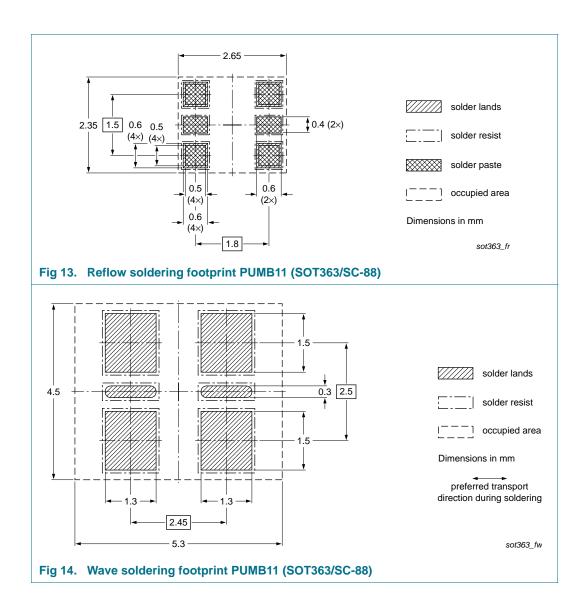
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	ackage Description		Packing quantity			
				3000	4000	8000	10000
PEMB11	SOT666	2 mm pitch, 8 mm tape and reel		-	-	-315	-
		4 mm pitch, 8 mm tape and reel		-	-115	-	-
PUMB11	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-	-165

- [1] For further information and the availability of packing methods, see Section 14.
- [2] T1: normal taping
- [3] T2: reverse taping

## 11. Soldering





PNP/PNP resistor-equipped transistors; R1 = 10 kΩ, R2 = 10 kΩ

## 12. Revision history

#### Table 10. Revision history

,							
Document ID	Release date	Data sheet status	Change notice	Supersedes			
PEMB11_PUMB11 v.3	20111130	Product data sheet	-	PEMB11_PUMB11 v.2			
Modifications:		of this document has been f NXP Semiconductors.	redesigned to com	ply with the new identity			
	<ul> <li>Legal texts h</li> </ul>	nave been adapted to the r	new company nam	e where appropriate.			
	<ul> <li>Section 1 "P</li> </ul>	roduct profile": updated					
	Section 4 "Marking": updated						
	• Table 7 "The	ermal characteristics": upda	ated according to the	ne latest measurements			
<ul> <li>Table 8 "Characteristics": I<sub>CEO</sub> updated according to the latest measurements, V<sub>i</sub>(V<sub>i(off)</sub> changed respectively to V<sub>I(on)</sub> and V<sub>I(off)</sub>, f<sub>T</sub> added</li> </ul>				test measurements, $V_{i(on)}$ and			
	• Figure 1 to 9	added :					
	Section 8 "Test information": added						
	<ul> <li>Figure 11 and 10: replaced by minimized package outline drawings</li> </ul>						
	<ul> <li>Section 10 "Packing information": added</li> </ul>						
	Section 11 "Soldering": added						
	<ul><li>Section 13 "</li></ul>	Legal information": update	d				
PEMB11_PUMB11 v.2	20031003	Product data sheet	-	PEMB11 v.1 PUMB11 v.1			
PEMB11 v.1	20010913	Preliminary specification	-	-			
PUMB11 v.1	20000808	Product specification	-	-			

## 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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PEMB11\_PUMB11

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PEMB11; PUMB11

PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$ 

**Quick reference data** — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

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## PNP/PNP resistor-equipped transistors; R1 = 10 kΩ, R2 = 10 kΩ

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